# **Chip Monolithic Ceramic Capacitors**



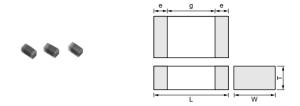
# **Low-dissipation Type**

### ■ Features

- 1. Mobile telecommunication and RF module, mainly
- 2. Quality improvement of telephone calls, Low power consumption, yield ratio improvement

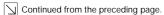
#### ■ Applications

VCO, PA, Mobile Telecommunications



Part Number	Dimensions (mm)						
Part Number	L	W	T	е	g min.		
GJM15	1.0 ±0.05	0.5 ±0.05	0.5 ±0.05	0.15 to 0.3	0.4		
GJM03	0.6 ±0.03	0.3 ±0.03	0.3 ±0.03	0.1 to 0.2	0.2		

Part Number	TC Code (Standard)	Rated Voltage (Vdc)	Capacitance (pF)	Length L (mm)	Width W (mm)	Thickness T (mm)
GJM1555C1HR50CB01	COG (EIA)	50	0.50 ±0.25pF	1.00	0.50	0.50
GJM1555C1HR75CB01	COG (EIA)	50	0.75 ±0.25pF	1.00	0.50	0.50
GJM1555C1H1R0CB01	COG (EIA)	50	1.0 ±0.25pF	1.00	0.50	0.50
GJM1555C1H1R1CB01	COG (EIA)	50	1.1 ±0.25pF	1.00	0.50	0.50
GJM1555C1H1R2CB01	COG (EIA)	50	1.2 ±0.25pF	1.00	0.50	0.50
GJM1555C1H1R3CB01	COG (EIA)	50	1.3 ±0.25pF	1.00	0.50	0.50
GJM1555C1H1R5CB01	COG (EIA)	50	1.5 ±0.25pF	1.00	0.50	0.50
GJM1555C1H1R6CB01	COG (EIA)	50	1.6 ±0.25pF	1.00	0.50	0.50
GJM1555C1H1R8CB01	COG (EIA)	50	1.8 ±0.25pF	1.00	0.50	0.50
GJM1555C1H2R0CB01	COG (EIA)	50	2.0 ±0.25pF	1.00	0.50	0.50
GJM1555C1H2R2CB01	COG (EIA)	50	2.2 ±0.25pF	1.00	0.50	0.50
GJM1555C1H2R4CB01	COG (EIA)	50	2.4 ±0.25pF	1.00	0.50	0.50
GJM1555C1H2R7CB01	COG (EIA)	50	2.7 ±0.25pF	1.00	0.50	0.50
GJM1555C1H3R0CB01	COG (EIA)	50	3.0 ±0.25pF	1.00	0.50	0.50
GJM1555C1H3R3CB01	COG (EIA)	50	3.3 ±0.25pF	1.00	0.50	0.50
GJM1555C1H3R6CB01	COG (EIA)	50	3.6 ±0.25pF	1.00	0.50	0.50
GJM1555C1H3R9CB01	COG (EIA)	50	3.9 ±0.25pF	1.00	0.50	0.50
GJM1555C1H4R0CB01	1555C1H4R0CB01 COG (EIA) 50		4.0 ±0.25pF	1.00	0.50	0.50
GJM1555C1H4R3CB01	C0G (EIA)	50	4.3 ±0.25pF	1.00	0.50	0.50
GJM1555C1H4R7CB01	C0G (EIA)	50	4.7 ±0.25pF	1.00	0.50	0.50
GJM1555C1H5R0CB01	C0G (EIA)	50	5.0 ±0.25pF	1.00	0.50	0.50
GJM1555C1H5R1CB01	C0G (EIA)	50	5.1 ±0.25pF	1.00	0.50	0.50
GJM1555C1H5R6CB01	COG (EIA)	50	5.6 ±0.25pF	1.00	0.50	0.50
GJM1555C1H6R0CB01	COG (EIA)	50	6.0 ±0.25pF	1.00	0.50	0.50
GJM1555C1H6R0DB01	COG (EIA)	50	6.0 ±0.5pF	1.00	0.50	0.50
GJM1555C1H6R2CB01	COG (EIA)	50	6.2 ±0.25pF	1.00	0.50	0.50
GJM1555C1H6R8CB01	COG (EIA)	50	6.8 ±0.25pF	1.00	0.50	0.50
GJM1555C1H7R0CB01	COG (EIA)	50	7.0 ±0.25pF	1.00	0.50	0.50
GJM1555C1H7R0DB01	COG (EIA)	50	7.0 ±0.5pF	1.00	0.50	0.50
GJM1555C1H7R5CB01	COG (EIA)	50	7.5 ±0.25pF	1.00	0.50	0.50
GJM1555C1H8R0CB01	COG (EIA)	50	8.0 ±0.25pF	1.00	0.50	0.50
GJM1555C1H8R0DB01	COG (EIA)	50	8.0 ±0.5pF	1.00	0.50	0.50
GJM1555C1H8R2CB01	COG (EIA)	50	8.2 ±0.25pF	1.00	0.50	0.50
GJM1555C1H9R0CB01	COG (EIA)	50	9.0 ±0.25pF	1.00	0.50	0.50
GJM1555C1H9R0DB01	COG (EIA)	50	9.0 ±0.5pF	1.00	0.50	0.50
GJM1555C1H9R1CB01	COG (EIA)	50	9.1 ±0.25pF	1.00	0.50	0.50
GJM1555C1H100JB01	COG (EIA)	50	10 ±5%	1.00	0.50	0.50
GJM1555C1H100RB01	C0G (EIA)	50	10 ±2.5%	1.00	0.50	0.50



Part Number	TC Code (Standard)	Rated Voltage (Vdc)	Capacitance (pF)	Length L (mm)	Width W (mm)	Thickness T (mm)	
GJM1555C1H120JB01	COG (EIA)	50	12 ±5%	1.00	0.50	0.50	
GJM1555C1H150JB01	COG (EIA)	50	15 ±5%	1.00	0.50	0.50	
GJM1555C1H180JB01	COG (EIA)	50	18 ±5%	1.00	0.50	0.50	

# **Specifications and Test Methods**

	Specifications		Specifications			
No.	Ite	Temperature Compensating Type		Test Method		
1	Operating Temperatu		−55 to +125°C			
2	2 Rated Voltage		See the previous pages	The rated voltage is defined as the maximum voltage which may be applied continuously to the capacitor.  When AC voltage is superimposed on DC voltage, V <sup>p,p</sup> or V <sup>o,p</sup> , whichever is larger, should be maintained within the rated voltage range.		
3	3 Appearance No defects or abnormalities		No defects or abnormalities	Visual inspection		
4	Dimensio	ons	Within the specified dimensions	Using calipers		
5	Dielectric	Strength	No defects or abnormalities	is applied between the	bserved when 300% of the rated voltage e terminations for 1 to 5 seconds, ischarge current is less than 50mA.	
6	Insulation (I.R.)	Resistance	10,000M $\Omega$ min. or 500 $\Omega$ • F min. (Whichever is smaller)		nce should be measured with a DC the rated voltage at 25°C and 75%RH utes of charging.	
7	Capacita	nce	Within the specified tolerance	•	ould be measured at 25℃ at the	
				frequency and voltage		
8	Q		30pF max. : Q≥400+20C C : Nominal Capacitance (pF)	Frequency	1±0.1MHz	
			, , , , , , , , , , , , , , , , , , ,	Voltage	0.5 to 5Vr.m.s.	
		Capacitance Change	Within the specified tolerance (Table A)	each specified temper	8	
		Temperature Coefficient	Within the specified tolerance (Table A)	Temperature Compensating Type The temperature coefficient is determined using the capacitance measured in step 3 as a reference.		
9	Capacitance Temperature Characteristics	Capacitance Drift	ure istics Capacitance	Within $\pm 0.2\%$ or $\pm 0.05$ pF (Whichever is larger.)	5, ( $\Delta$ C: +25°C to+125°the capacitance shoul temperature coefficien. The capacitance drift is between the maximum 1, 3 and 5 by the capacitance.	perature sequentially from step 1 through ${}^{\circ}\mathbb{C}$ : other temp. coeffs. : $+25{}^{\circ}\mathbb{C}$ to $85{}^{\circ}\mathbb{C}$ ) d be within the specified tolerance for the nt and capacitance change as Table A. is calculated by dividing the differences n and minimum measured values in steps acitance value in step 3.  Temperature ( ${}^{\circ}\mathbb{C}$ )  25±2
				3		
				4	125±3	
				5	25±2	
10	Adhesive of Termin		No removal of the terminations or other defect should occur.	Solder the capacitor to the test jig (glass epoxy board) s Fig. 1 using a eutectic solder. Then apply a 5N* force in with the test jig for 10±1sec. The soldering should be d with an iron or using the reflow method and should be of with care so that the soldering is uniform and free of def as heat shock.  *2I  Solder resir  Baked elec copper foil  Type a b GJM03 0.3 0.9 0.9 Fig. 1		

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# **Specifications and Test Methods**

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7	Continued fr	om the prec						
No.	lt.c	em	Specifications	Test Method				
NO.	i iii	3111	Temperature Compensating Type	rest Method				
11	Vibration Resistance	Appearance Capacitance  Q	No defects or abnormalities  Within the specified tolerance  30pF max. : Q≥400+20C C : Nominal Capacitance (pF)	Solder the capacitor to the test jig (glass epoxy board) in the same manner and under the same conditions as (10).  The capacitor should be subjected to a simple harmonic mo having a total amplitude of 1.5mm, the frequency being varie uniformly between the approximate limits of 10 and 55Hz. The frequency range, from 10 to 55Hz and return to 10Hz, should be traversed in approximately 1 minute. This motion should be applied for a period of 2 hours in each of 3 mutual perpendicular directions (total of 6 hours).				
	12 Deflection		No cracking or marking defects should occur	Solder the capacitor to the test jig (glass epoxy boards) shown in Fig. 2 using a eutectic solder.  Then apply a force in the direction shown in Fig. 3.  The soldering should be done either with an iron or using the reflow method and should be conducted with care so that the soldering is uniform and free of defects such as heat shock.  20 50 Pressurizing speed: 1.0mm/sec. Pressurize  Flexure: ≤1  Capacitance meter  45  (in mm)  Fig. 3				
12			Type a b c GJM03 0.3 0.9 0.3 GJM15 0.4 1.5 0.5 (in mm)					
13	Solderab Terminati	•	75% of the terminations are to be soldered evenly and continuously.	Immerse the capacitor in a solution of ethanol (JIS-K-8101) and rosin (JIS-K-5902) (25% rosin in weight proportion).  Preheat at 80 to 120°C for 10 to 30 seconds. After preheating, immerse in eutectic solder solution for 2±0.5 seconds at 230±5				
			The measured and observed characteristics should satisfy the specifications in the following table.					
		Appearance	No marking defects					
14	Resistance to Soldering	Capacitance Change	Within ±2.5% or ±0.25pF (Whichever is larger)	Preheat the capacitor at 120 to 150°C for 1 minute.  Immerse the capacitor in a eutectic solder solution at 270±5°C				
•	Heat	Q	30pF and below : Q≥400+20C C : Nominal Capacitance (pF)	for 10±0.5 seconds.  Let sit at room temperature for 24±2 hours.				
		I.R.	More than 10,000MΩ or 500Ω • F (Whichever is smaller)					
		Dielectric Strength	No failure					
		The measured and observed characteristics should satisfy the specifications in the following table.						
		Appearance	No marking defects	Fix the capacitor to the supporting jig in the same manner and under the same conditions as (10). Perform the five cycles				
	Tomporetina	Capacitance Change	Within ±2.5% or ±0.25pF (Whichever is larger)	according to the four heat treatments listed in the following table Let sit for 24±2 hours at room temperature, then measure.				
15	Temperature Cycle	Q	30pF and below : Q≥400+20C C : Nominal Capacitance (pF)	Step 1 2 3 4				
		I.R.	More than 10,000MΩ or 500Ω • F (Whichever is smaller)	тепр.—з тетр. тепр.—о тетр.				
		Dielectric Strength	No failure	Time (min.)  30±3   2 to 3   30±3   2 to 3				
			The measured and observed characteristics should satisfy the specifications in the following table.					
		Appearance	No marking defects					
16	Humidity, Steady	Capacitance Change	Within ±5% or ±0.5pF (Whichever is larger)	Let the capacitor sit at 40±2°C and 90 to 95% humidity for 500±12 hours.				
	State	Q	10pF and over, 30pF and below : Q≥275+ ½ C 10pF and below : Q≥200+10C C : Nominal Capacitance (pF)	Remove and let sit for 24±2 hours (temperature compensating type) at room temperature, then measure.				
		I.R.	More than 10,000M $\Omega$ or 500 $\Omega$ • F (Whichever is smaller)					

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### **Specifications and Test Methods**

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			Specifications			
No.	lte	em	Temperature Compensating Type	Test Method		
17			The measured and observed characteristics should satisfy the specifications in the following table.			
		Appearance	No marking defects			
	Humidity	Capacitance Change	Within ±7.5% or ±0.75pF (Whichever is larger)	Apply the rated voltage at 40±2℃ and 90 to 95% humidity for 500±12 hours.		
	Load	Q	30pF and below : Q≥100+ ½ C C : Nominal Capacitance (pF)	Remove and let sit for 24±2 hours at room temperature, then measure. The charge/discharge current is less than 50mA.		
		I.R.	More than 500MΩ or 25Ω • F (Whichever is smaller)			
		Dielectric Strength No failure				
			The measured and observed characteristics should satisfy the specifications in the following table.			
		Appearance	No marking defects			
	High	Capacitance Change	Within ±3% or ±0.3pF (Whichever is larger)	Apply 200% of the rated voltage for 1000±12 hours at the maximum operating temperature ±3°C. Let sit for 24±2 hours		
18	Temperature Load	Q	10pF and over, 30pF and below : Q≥275+ ½ C 10pF and below : Q≥200+10C C : Nominal Capacitance (pF)	(temperature compensating type) at room temperature, then measure.  The charge/discharge current is less than 50mA.		
		I.R.	More than 1,000M $\Omega$ or 50 $\Omega$ • F (Whichever is smaller)			
		Dielectric Strength	No failure			
19	ESR		0.5pF≦C≦1pF : 350mΩ • pF below 1pF <c≦5pf 300mω="" :="" below<br="">5pF<c≦10pf 250mω="" :="" below<="" td=""><td>The ESR should be measured at room Temperature. and frequency 1±0.2GHz with the equivalent of BOONTON Model 34A.</td></c≦10pf></c≦5pf>	The ESR should be measured at room Temperature. and frequency 1±0.2GHz with the equivalent of BOONTON Model 34A.		
			10pF <c≦20pf 400mω="" :="" below<="" td=""><td>The ESR should be measured at room Temperature. and frequency 500±50MHz with the equivalent of HP8753B.</td></c≦20pf>	The ESR should be measured at room Temperature. and frequency 500±50MHz with the equivalent of HP8753B.		

### Table A

Char. Code	Temp. Coeff. (ppm/°C) Note 1	Capacitance Change from 25℃ Value (%)					
		<b>−55℃</b>		−30°C		−10℃	
	(ррпії с) чосе т	Max.	Min.	Max.	Min.	Max.	Min.
5C	0±30	0.58	-0.24	0.40	-0.17	0.25	-0.11

Note 1 : Nominal values denote the temperature coefficient within a range of 25 to 125°C.(for ΔC)